

L Number	Hits	Search Text	DB	Time stamp
	4809	((438/149-154) or (257/347-352) or (257/59,72) or (348/46)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/15 09:49
	7	("5698869") or ("5728592").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/06 16:24
	71	((("438/149-154") or ("257/347-352") or ("257/59,72") or ("348/46"))).CCLS.) and ((anodizing or anodically or anodized) near (oxide or oxygen or oxidized))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/07 09:34
	266	((thin adj film adj transistor) or TFT) and ((anodically or anodizing or anode) near (oxidized or oxidizing or oxidized))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/07 09:55
	29	((thin adj film adj transistor) or TFT) and ((anodically or anodizing or anode) near (oxidized or oxidizing or oxidized)) and (angled or tapered or tapered)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/07 09:57
	396	((photoresist or resist or (photo adj resist)) near (bake or baked)) same temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/07 12:10
	9	((photoresist or resist or (photo adj resist)) near (bake or baked)) same temperature and (TFT or (thin adj film adj transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/07 12:11
	586	anodically adj oxidizing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/07 13:29
	1	("5202274").PN.	USPAT	2002/03/07 13:00
	20	5202274.URPN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/07 13:02
	0	(anodically adj oxidizing) near (advantage or advantages)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/07 13:30
	4	(anodically adj oxidizing) same (advantage or advantages)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/07 13:30
	0	((anodic or anodical) near (oxidiz\$3)) same (Al or aluminum) and ((native near oxide) same (etch or etched or etching))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/15 09:52
	1562	(Al or aluminum) and ((native near oxide) same (etch or etched or etching))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/15 09:52
	326	(Al or aluminum) same ((native near oxide) same (etch or etched or etching))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/15 09:52

		0 (Al or aluminum) same ((native near oxide) same (etch or etched or etching)) and (anodically near oxidizing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/15 09:53
	286	(Al or aluminum) same ((native near oxide) same (etch or etched or etching)) and (semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/15 09:54
	252	(Al or aluminum) same ((native near oxide) same (etch or etched or etching)) and (semiconductor)	USPAT; DERWENT; IBM_TDB	2003/04/15 09:55
	20	(plasma near chamber) same (cooling near medium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/04/15 14:09
	18	(plasma near chamber) same (cooling near medium)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/04/15 14:12
	82	(plasma near chamber) same (cool\$4 with substrate)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/04/15 15:04
	306	antifuse with oxide	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/04/15 15:04
	240	(antifuse with oxide) and semiconductor	USPAT; EPO; JPO; DERWENT; IBM_TDB	2003/04/15 15:04
	175	(438/466).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/11 09:25
	24	((438/466).CCLS.) and anodic\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/11 10:51
	13	((438/466).CCLS.) and anodic\$4 and (thin near (film or layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/11 10:51